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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.



INFORMATION DISCLOSURE CITATION IN AN APPLICATION

ATTY. DOCKET NO. **57454-224**

SERIAL NO.

09/982936 09/982936 09/22/01

(PTO-1449)

Hideto HIDAKA

APPLICANT

FILING DATE
October 22, 2001

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EXAMINER

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4/02